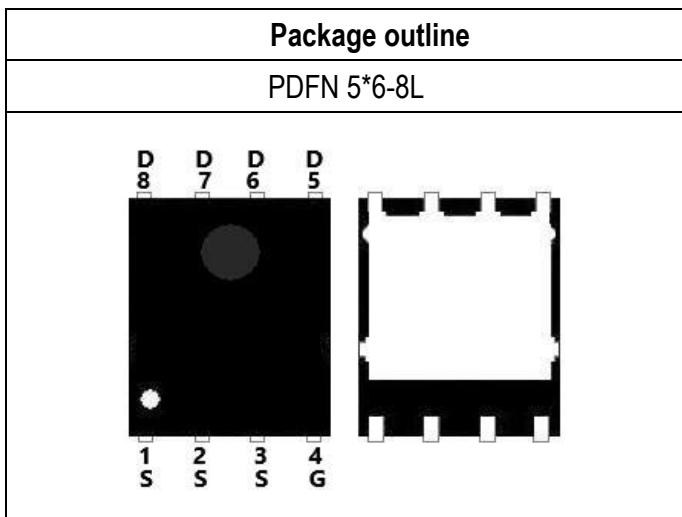


Key parameter	Value	Unit
$V_{(BR)DSS}$ min.	100	V
$R_{DS(ON)}$ max. $V_{GS}=10V$	4.7	$m\Omega$
I_D	90.4	A
C_{iss} Typ.	5883	pF
Q_g 10V Typ.	86.6	nC



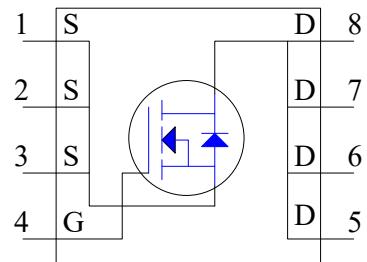
Description

These devices used double-gate structure of MOSFET to provide excellent electrical parameter. There is high speed switching capacity, low $R_{DS(ON)}$ resistance, low gate charge and stable characteristics for these devices. Moreover, it is a helpful choose for raise efficiency or reduce consumption in circuit. These features combine to be an advantage design for use in wide variety of application including converter and inverter design.

Features

- ◇ Fast switch capacity
- ◇ Low $R_{DS(ON)}$ resistance
- ◇ Low input capacitance
- ◇ Pb-free lead plating; RoHS compliant

Symbol and Pin assignment



Potential application

- AC to DC adaptor
- DC to DC Converter
- Power Switch Mode Supply
- Network equipment and display power supply unit

Order Information

Item	Description
1. Order Code	DG100N43HQ
2. Part Number	DG100N43HQ
3. Package Type	PDFN 5*6-8L
4. Package Code	Q
5. Packing Type	Tape & Reel
6. Quantity in Pack	2,500
7. RoHS Status	Halogen-Free

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2.	Thermal Resistance Ratings -----	3
3.	Electrical Characteristics -----	4
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1. Absolute Maximum Ratings (T_J=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	V _{DS}	100	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous ^{Note 1}	T _C =25°C	I _D	90.4	A
	T _C =100°C		57.2	A
Drain Current-Continuous ^{Note 2}	T _A =25°C	I _D	15.8	A
	T _A =70°C		12.7	A
Drain Current-Pulsed ^{Note 3}	T _A =25°C	I _{DM}	200	A
Avalanche Current	I _{AR}	63.1	A	
Single Pulse Avalanche Energy ^{Note 4}	E _{AS}	199	mJ	
Maximum Power Dissipation	T _C =25°C	P _D	65.1	W
	T _C =100°C		26.0	W
	T _A =25°C		2.0	W
	T _A =70°C		1.28	W
	Derate Factor Above T _C =25°C		0.52	W/°C
Max. Operating Junction Temperature	T _J	150	°C	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C	

2. Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-Case	R _{θJC-N}	Please refer to Notes ^{Note 5}	-	-	1.92	°C/W
Thermal resistance, Junction-Ambient	R _{θJA-N}	Please refer to Notes ^{Note 5}	-	-	62.26	°C/W

Notes:

1. Limited by silicon chip capability and R_{θJC-N} junction-to-case thermal resistance.
2. The maximum current rating is limited by package and R_{θJA-N} junction-to-ambient thermal resistance.
3. Must be ensure junction temperature does not exceed 150-degree C. (Pulse Width \leq 380uS, Duty \leq 2%)
4. Limited by T_{Jmax}, starting T_J=25°C, L=0.1mH, R_g=25Ω, I_D=63.1A, V_{GS}=10V.
5. The value of thermal resistance is measured with the single device mounted on 1 inch² FR-4 PCB with 2 oz. copper under a still air environment temperature is 25°C based on JEDEC standard JESD51-14 and JESD51-2a. Thermal resistance obtained depends on the user's specific board design and given application.

3. Electrical Characteristics (T_J=25°C unless otherwise noted)

STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _{DS} =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =125°C	-	-	100	μA
Gate-Body Leakage	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

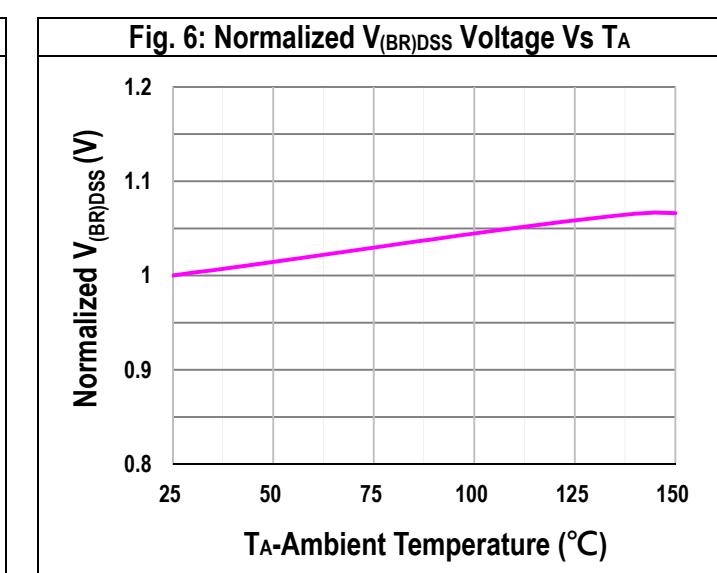
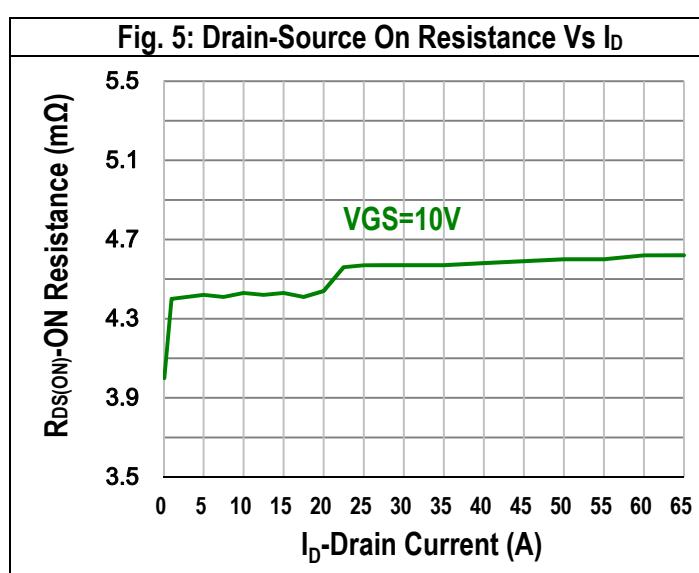
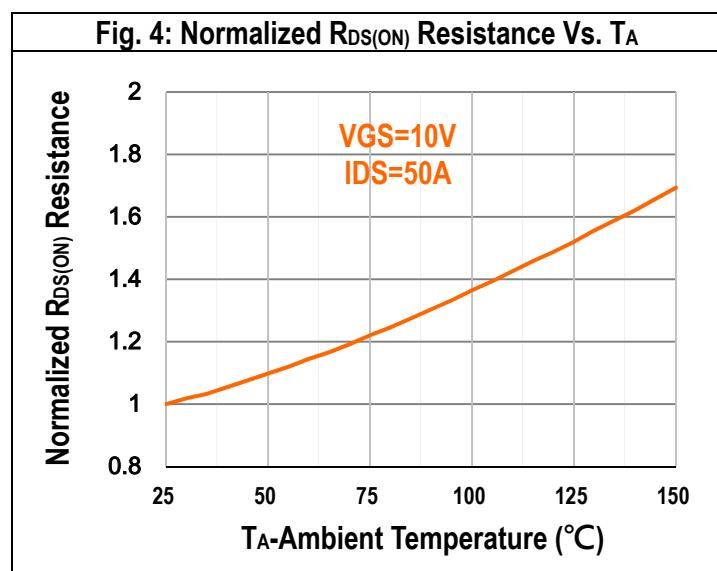
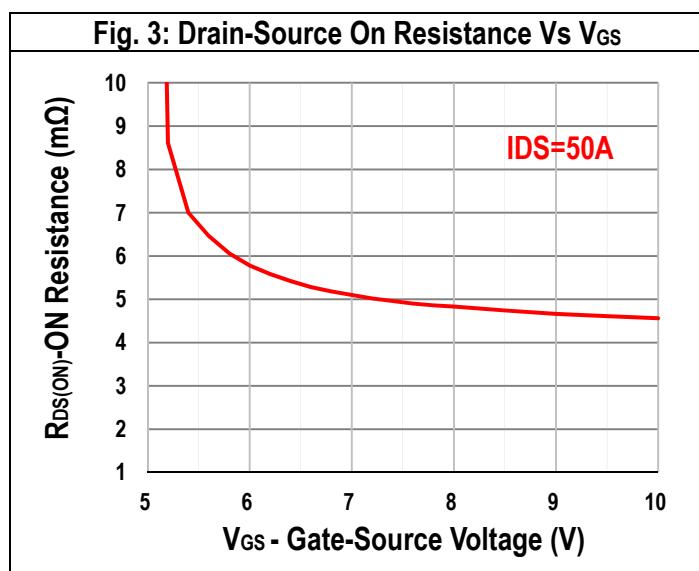
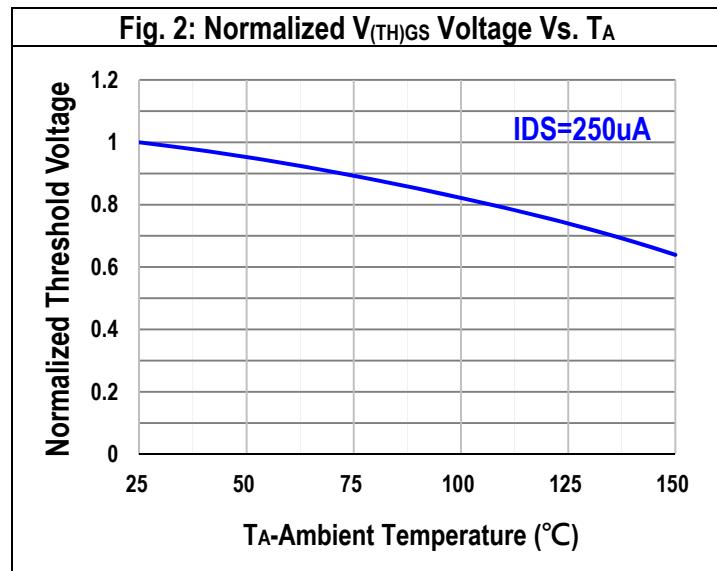
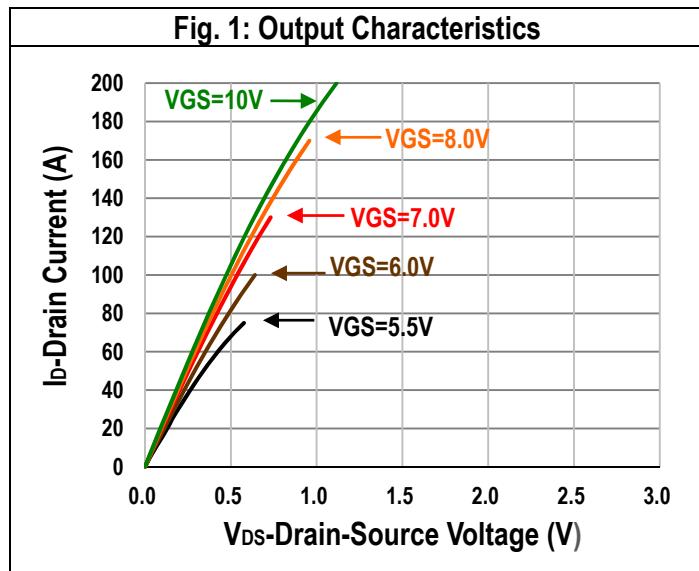
STATIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250μA	2	-	4	V
Drain-Source On-State Resistance	R _{D(S)ON}	V _{GS} =10V, I _{DS} =20A	-	3.9	4.7	mΩ
Drain-Source On-State Resistance	R _{D(S)ON}	V _{GS} =6V, I _{DS} =20A	-	5.7	6	mΩ
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	-	1.3	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =5V, I _{DS} =20A	-	31.9	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{iss}	V _{DD} =100V, V _{DS} =50V, V _{GS} =0V, F=1MHz	-	5883	-	pF
Output Capacitance	C _{oss}	V _{DD} =100V, V _{DS} =50V, V _{GS} =0V, F=1MHz	-	898	-	pF
Reverse Transfer Capacitance	C _{rss}	V _{DD} =100V, V _{DS} =50V, V _{GS} =0V, F=1MHz	-	26.3	-	pF
Turn-On Delay Time	T _{d(on)}	V _{DS} =50V, V _{GS} =10V, I _{DS} =50A, R _{GEN} =3.0Ω	-	23.3	-	nS
Rise Time	T _r	V _{DS} =50V, V _{GS} =10V, I _{DS} =50A, R _{GEN} =3.0Ω	-	50.5	-	nS
Turn-Off Delay Time	T _{d(off)}	V _{DS} =50V, V _{GS} =10V, I _{DS} =50A, R _{GEN} =3.0Ω	-	46.8	-	nS
Fall Time	T _f	V _{DS} =50V, V _{GS} =10V, I _{DS} =50A, R _{GEN} =3.0Ω	-	30	-	nS

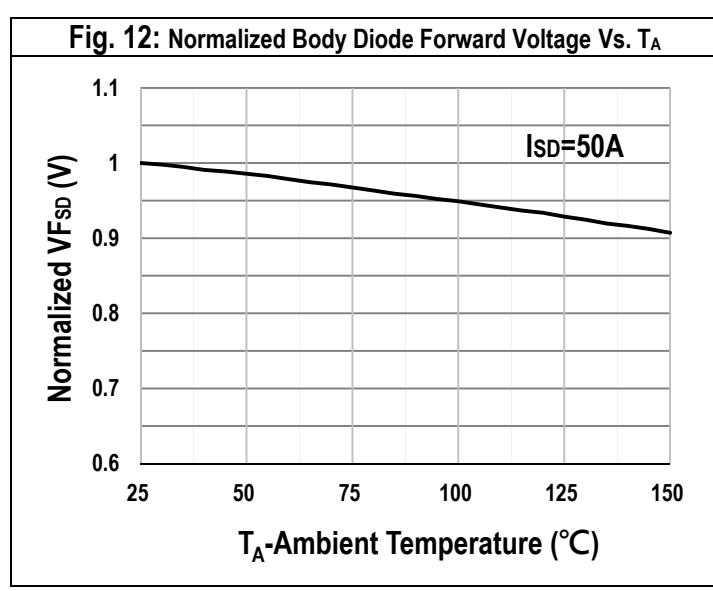
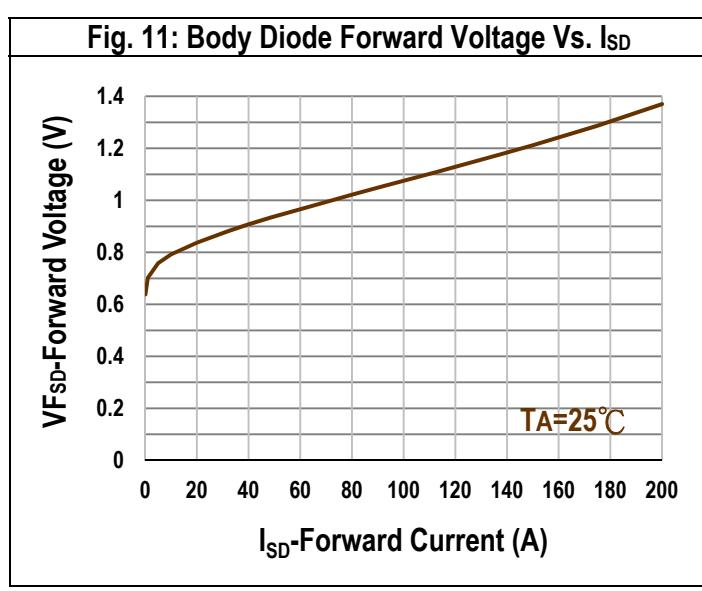
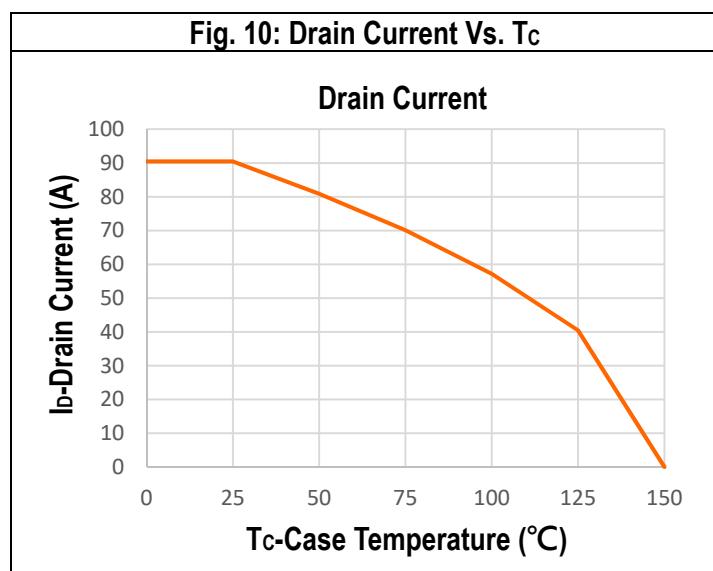
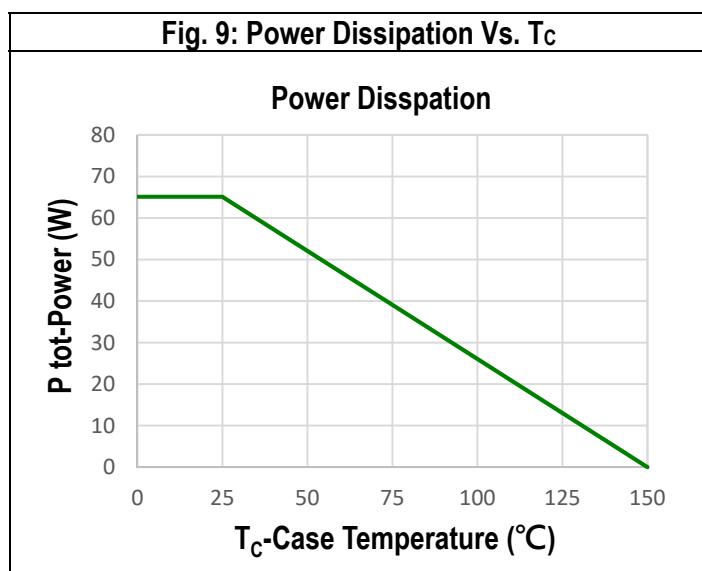
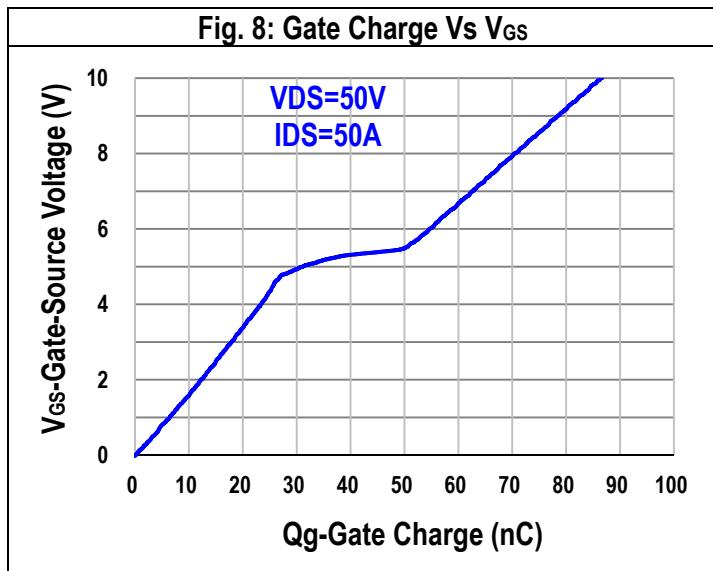
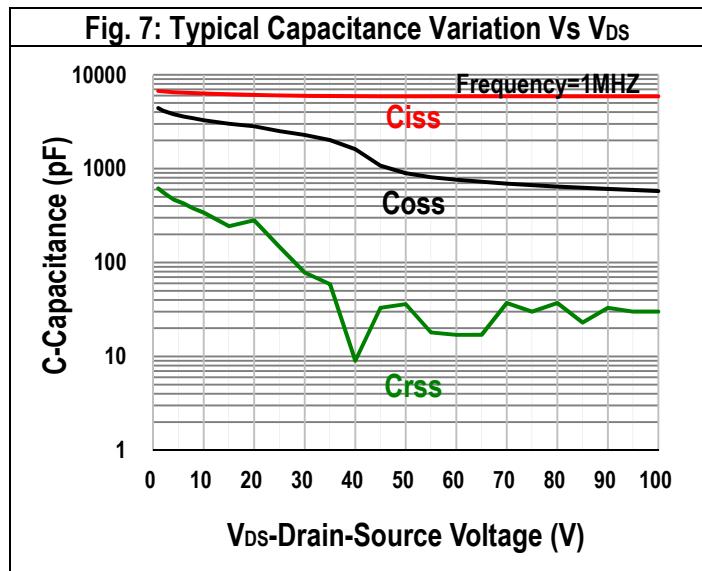
GATE CHARGE CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate to Source Gate Charge	Q _{gs}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	32.1	-	nC
Gate charge at threshold	Q _{g(th)}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	19	-	nC
Gate to Drain Charge	Q _{gd}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	18.3	-	nC
Switching charge	Q _{SW}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	31.4	-	nC
Total gate charge	Q _{g 10V}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	86.6	-	nC
Gate plateau voltage	V _{plateau}	V _{DD} =50V, I _D =50A, V _{GS} =0 to 10V	-	5.3	-	V
Total gate charge, sync. FET (Q _g -Q _{gd})	Q _{g(sync)}	V _{DS} =0.1V, V _{GS} =0 to 10V	-	68.3	-	nC

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Body Diode continuous forward current	I _{SD}	T _C =25°C	-	-	90.4	A
Body Diode pulse current	I _{SM}	T _C =25°C	-	-	200	A
Body Diode Forward Voltage	V _{FSD}	V _{GS} =0V, I _S =50A	-	0.94	1.0	V
Body Diode Reverse Recovery Time	t _{rr}	V _{DD} =50V, I _F =50A, di/dt=100A/μs	-	70	-	nS
Body Diode Reverse Recovery Charge	Q _{rr}	V _{DD} =50V, I _F =50A, di/dt=100A/μs	-	101	-	nC
Body Diode Reverse Recovery Current	I _{rrm}	V _{DD} =50V, I _F =50A, di/dt=100A/μs	-	-2.57	-	A

4. Typical Operating Characteristics Diagram



4. Typical Operating Characteristics Diagram



4. Typical Operating Characteristics Diagram

Fig. 13: Safe Operation Area

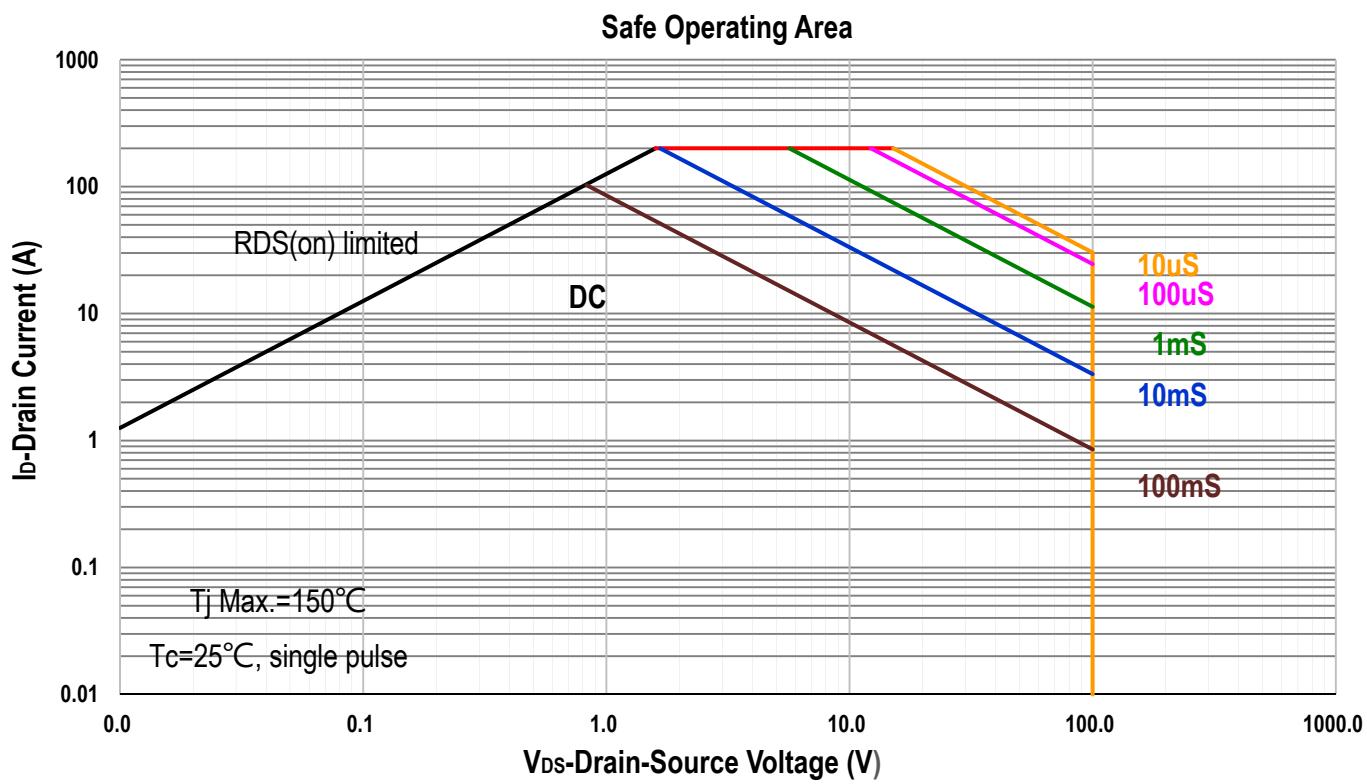
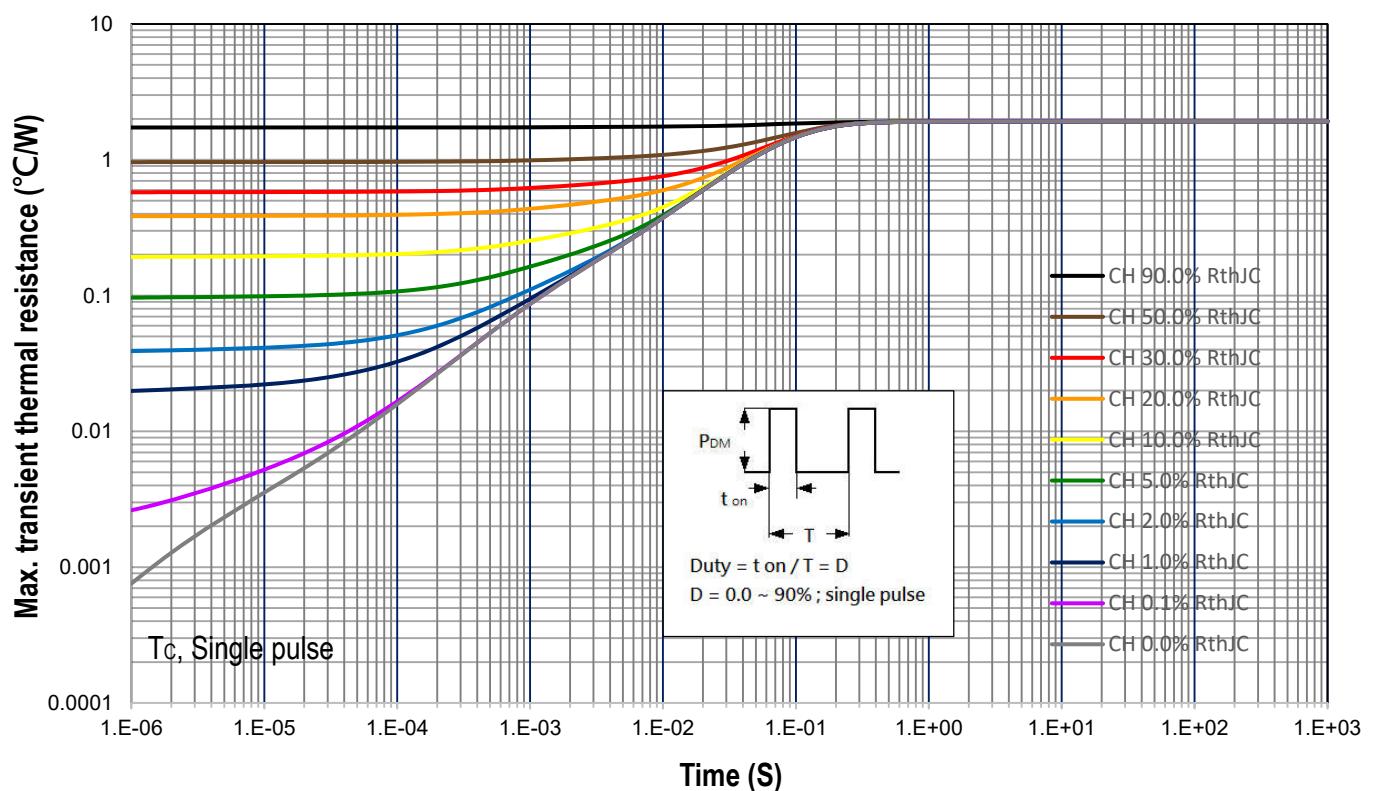
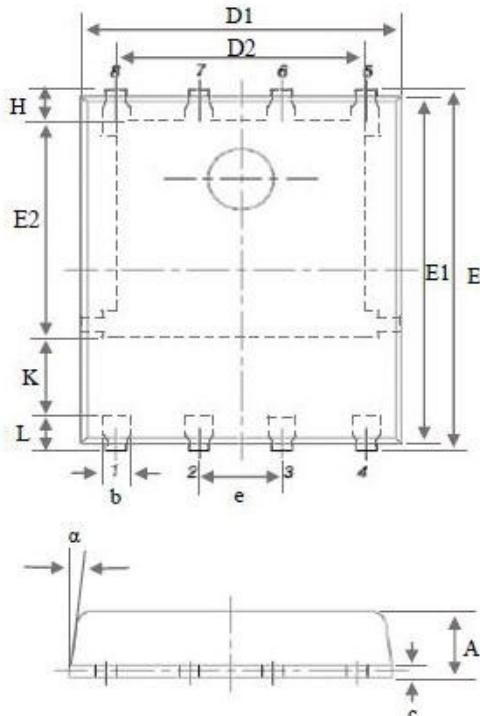


Fig. 14: Transient Thermal Impedance



5. Package of Dimension

Package type: PDFN 5*6-8L

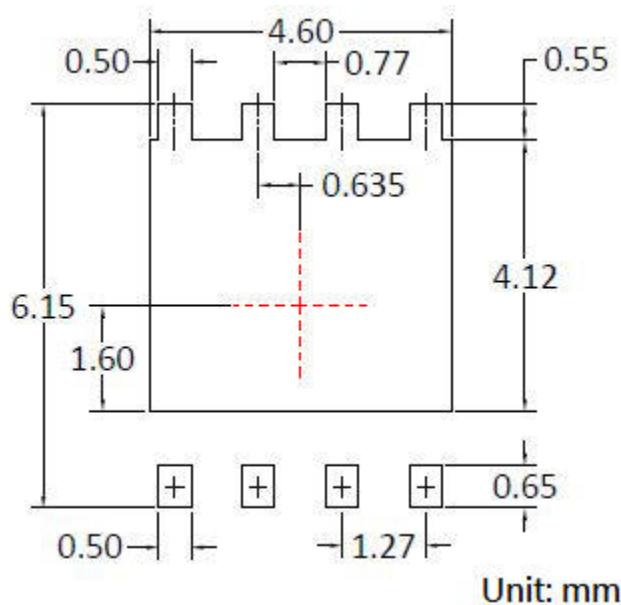


Symbol	Min	Nor	Max
A	0.90	1.04	1.17
b	0.33	0.42	0.51
C	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e	1.27 BSC		
H	0.38	0.50	0.61
L	0.38	0.55	0.71
L1	0.05	0.15	0.25

Unit : mm

1. All dimension are in millimeters.
2. Dimension does not include burrs and flash/protrusions.

6. Land pattern (Footprint)



Note 1: Land pattern (Footprint) design is for reference only.

Note 2: Package body sizes exclude mold flash and burrs.

Note 3: Dimension is measured in gauge plane.

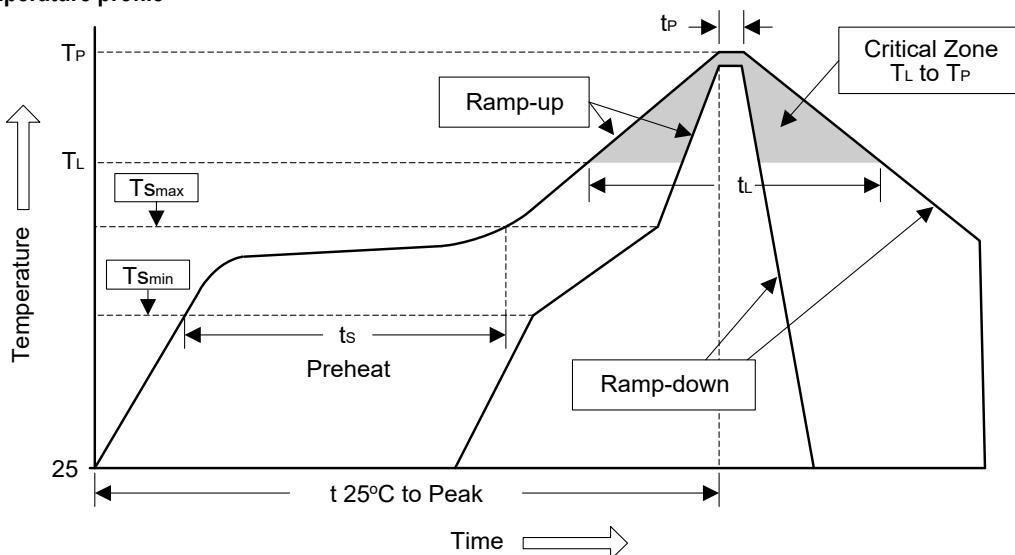
Note 4: Tolerance 0.1mm unless otherwise specified.

7. Appendix-A

Soldering Methods for Silicongear's Products (Just for SMD type of device)

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{Smin})	100°C	150°C
- Temperature Max (T _{Smax})	150°C	200°C
- Time (min to max) (t _s)	60 to 120 sec	60 to 180 sec
T _{Smax} to T _L	<3°C/sec	<3°C/sec
- Ramp-up Rate		
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _P)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec

8. Appendix-B**Important Notice****© Silicongear Corporation**

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